



AOS Semiconductor Product Reliability Report

AO5600E/AO5600EL, rev A

Plastic Encapsulated Device

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Jul 14, 2008

This AOS product reliability report summarizes the qualification result for AO5600E. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO5600E passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

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I. Product Description:

The AO5600E uses advanced trench technology MOSFETs to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs may be used in H-bridge, Inverters and other applications.
 -RoHS compliant

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted				
Parameter	Symbol	Max n-ch	Max p-ch	Units
Drain-Source Voltage	V_{DS}	20	-20	V
Gate-Source Voltage	V_{GS}	±8		V
Continuous Drain Current	$T_A=25^\circ\text{C}$	0.6	-0.5	A
	$T_A=70^\circ\text{C}$	I_D	-0.38	
Pulsed Drain Current	I_{DM}	3	-1	
Power Dissipation	$T_A=25^\circ\text{C}$	P_D	0.38	W
	$T_A=70^\circ\text{C}$		0.24	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150		$^\circ\text{C}$

Thermal Characteristics					
Parameter: n-ch and p-ch	Symbol	Typ	Max	Units	
Maximum Junction-to-Ambient	$T \leq 10\text{s}$	$R_{\theta JA}$	275	330	$^\circ\text{C/W}$
Maximum Junction-to-Ambient	Steady-State		360	450	$^\circ\text{C/W}$
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	300	350	$^\circ\text{C/W}$

II. Die / Package Information:

	AO5600E	AO5600EL (Green Compound)
Process	Standard sub-micron	Standard sub-micron
Package Type	Low voltage N channel process	Low voltage N channel process
Lead Frame	SC89	SC89
Die Attach	Alloy 42, D/pad, Ag lead	Alloy 42, D/pad, Ag lead
Bond wire	Eutectic	Eutectic
Mold Material	Au 0.8mils	Au 0.8mils
Filler % (Spherical/Flake)	Epoxy resin with silica filler	Epoxy resin with silica filler
Flammability Rating	90/10	100/0
Backside Metallization	UL-94 V-0	UL-94 V-0
Moisture Level	Ti / Ni / Ag	Ti / Ni / Ag
	Up to Level 1 *	Up to Level 1 *

Note * based on info provided by assembler and mold compound supplier

III. Result of Reliability Stress for AO5600E (Standard) & AO5600EL (Green)

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures
Solder Reflow Precondition	Standard: 1hr PCT+3 cycle reflow@260°C Green: 168hr 85°C /85%RH +3 cycle reflow@260°C	0hr	Standard: 10 lots Green: 2 lots	2546 pcs	0
HTGB	Temp = 150°C , Vgs=100% of Vgsmax	168 / 500 hrs 1000 hrs	2 lots (Note A*)	164 pcs 77+5 pcs / lot	0
HTRB	Temp = 150°C , Vds=80% of Vdsmax	168 / 500 hrs 1000 hrs	2 lots (Note A*)	164 pcs 77+5 pcs / lot	0
HAST	130 +/- 2°C , 85%RH, 33.3 psi, Vgs = 80% of Vgs max	100 hrs	Standard: 10 lots Green: 2 lots (Note B**)	660 pcs 50+5 pcs / lot	0
Pressure Pot	121°C , 29.7psi, 100%RH	96 hrs	Standard: 9 lots Green: 2 lots (Note B**)	902 pcs 77+5 pcs / lot	0
Temperature Cycle	-65°C to 150°C , air to air	250 / 500 cycles	Standard: 10 lots Green: 2 lots (Note B**)	984 pcs 77+5 pcs / lot	0

III. Result of Reliability Stress for AO5600E (Standard) & AO5600EL (Green) Continues

DPA	Internal Vision Cross-section X-ray	NA	5 5 5	5 5 5	0
CSAM		NA	5	5	0
Bond Integrity	Room Temp 150°C bake 150°C bake	0hr 250hr 500hr	40 40 40	40 wires 40 wires 40 wires	0
Solderability	245°C	5 sec	15	15 leads	0

Note A: The HTGB and HTRB reliability data presents total of available AO5600E and AO5600EL burn-in data up to the published date.

Note B: The pressure pot, temperature cycle and HAST reliability data for AO5600E and AO5600EL comes from the AOS generic package qualification data.

IV. Reliability Evaluation

FIT rate (per billion): 64

MTTF = 1783 years

In general, 500 hrs of HTGB, 150 deg C accelerated stress testing is equivalent to 15 years of lifetime at 55 deg C operating conditions (by applying the Arrhenius equation with an activation energy of 0.7eV and 60% of upper confidence level on the failure rate calculation). AOS reliability group also routinely monitors the product reliability up to 1000 hr at and performs the necessary failure analysis on the units failed for reliability test(s).

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AO5600E). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

$$\text{Failure Rate} = \text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)] = 1.83 \times 10^9 / [2 (2 \times 164) (168) (258)] = 64$$

$$\text{MTTF} = 10^9 / \text{FIT} = 1.56 \times 10^7 \text{hrs} = 1783 \text{ years}$$

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from HTRB and HTGB tests

H = Duration of HTRB/HTGB testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

$$\text{Acceleration Factor [Af]} = \text{Exp} [Ea / k (1/Tj u - 1/Tj s)]$$

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	258	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u = The use junction temperature in degree (Kelvin), K = C+273.16

k = Boltzmann's constant, 8.617164 X 10⁻⁵eV / K



V. Quality Assurance Information

Acceptable Quality Level for outgoing inspection: **0.1%** for electrical and visual.

Guaranteed Outgoing Defect Rate: **< 25 ppm**

Quality Sample Plan: conform to **Mil-Std-105D**